

Joseph Woicik

List of Publications by Year in descending order

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101
papers

3,627
citations

136950
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101
all docs

101
docs citations

101
times ranked

4689
citing authors

#	ARTICLE	IF	CITATIONS
1	A Ferroelectric Oxide Made Directly on Silicon. <i>Science</i> , 2009, 324, 367-370.	12.6	347
2	Diffraction anomalous fine structure: A new x-ray structural technique. <i>Physical Review Letters</i> , 1992, 69, 3064-3067.	7.8	217
3	Surface extended-x-ray-absorption fine structure and scanning tunneling microscopy of Si(001)2Å-1-Sb. <i>Physical Review Letters</i> , 1990, 65, 3417-3420.	7.8	141
4	Oxygen vacancies in N doped anatase TiO ₂ : Experiment and first-principles calculations. <i>Applied Physics Letters</i> , 2009, 95, .	3.3	140
5	Origin of the Bipolar Doping Behavior of SnO from X-ray Spectroscopy and Density Functional Theory. <i>Chemistry of Materials</i> , 2013, 25, 3114-3123.	6.7	135
6	Near-neighbor mixing and bond dilation in mechanically alloyed Cu-Fe. <i>Physical Review B</i> , 1996, 54, 6929-6940.	3.2	124
7	Direct Observation of Electrostatically Driven Band Gap Renormalization in a Degenerate Perovskite Transparent Conducting Oxide. <i>Physical Review Letters</i> , 2016, 116, 027602.	7.8	100
8	Nature of the Metal Insulator Transition in Ultrathin Epitaxial Vanadium Dioxide. <i>Nano Letters</i> , 2013, 13, 4857-4861.	9.1	90
9	La-doped BaSnO ₃ “Degenerate perovskite transparent conducting oxide: Evidence from synchrotron x-ray spectroscopy. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	81
10	X-Ray Anomalous Scattering Study of a Charge-Ordered State in NaV ₂ O ₅ . <i>Physical Review Letters</i> , 2000, 85, 4349-4352.	7.8	73
11	Gold-induced germanium crystallization. <i>Physical Review B</i> , 1992, 46, 9505-9510.	3.2	72
12	Surface structure of cadmium selenide nanocrystallites. <i>Physical Review B</i> , 1997, 55, 13822-13828.	3.2	70
13	Bond-Length Distortions in Strained Semiconductor Alloys. <i>Physical Review Letters</i> , 1997, 79, 5026-5029.	7.8	69
14	Origin of deep subgap states in amorphous indium gallium zinc oxide: Chemically disordered coordination of oxygen. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	67
15	Selective Passivation of GeO ₂ /Ge Interface Defects in Atomic Layer Deposited High-k MOS Structures. <i>ACS Applied Materials & Interfaces</i> , 2015, 7, 20499-20506.	8.0	66
16	Displacive Ordering Transitions in Perovskite-Like AgNb _{1/2} Ta _{1/2} O ₃ . <i>Chemistry of Materials</i> , 2010, 22, 4987-4995.	6.7	63
17	Stability of the M2 phase of vanadium dioxide induced by coherent epitaxial strain. <i>Physical Review B</i> , 2016, 94, .	3.2	62
18	Conservation of bond lengths in strained Ge-Si layers. <i>Physical Review B</i> , 1991, 43, 2419-2422.	3.2	59

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19	Strontium-induced oxygen defect structure and hole doping in $\text{La}_{2-x}\text{Sr}_x\text{CuO}_4$. Physical Review Letters, 1990, 64, 2715-2718.	7.8	55
20	Band-structure effects in the excitation-energy dependence of $\text{SiL}_{2,3}$ -x-ray-emission spectra. Physical Review B, 1993, 48, 1918-1920.	3.2	54
21	Accommodation of strain in ultrathin InAs/GaAs films. Physical Review B, 1995, 52, R2281-R2284.	3.2	54
22	Local atomic and electronic structures of epitaxial strained LaCoO_3 thin films. Physical Review B, 2012, 85, .	3.2	54
23	A combined fit of total scattering and extended X-ray absorption fine structure data for local-structure determination in crystalline materials. Journal of Applied Crystallography, 2009, 42, 867-877.	4.5	51
24	Extended x-ray absorption fine structure study of $\text{Al}_x\text{Ga}(1-x)\text{N}$ films. Applied Physics Letters, 1997, 70, 2108-2110.	3.3	49
25	X-ray standing-wave determination of the clean InP(110) surface reconstruction. Physical Review Letters, 1992, 68, 341-344.	7.8	45
26	Strain-induced change in local structure and its effect on the ferromagnetic properties of $\text{La}_{0.5}\text{Sr}_{0.5}\text{CoO}_3$ thin films. Applied Physics Letters, 2008, 93, 182507.	3.3	42
27	In situ XANES of an iron porphyrin irreversibly adsorbed on an electrode surface. Journal of the American Chemical Society, 1991, 113, 9063-9066.	13.7	38
28	Interfacial Effects in $\mu\text{-Li}_{x}\text{VOPO}_4$ and Evolution of the Electronic Structure. Chemistry of Materials, 2015, 27, 8211-8219.	6.7	37
29	Performance of a four-element Si drift detector for X-ray absorption fine-structure spectroscopy: resolution, maximum count rate, and dead-time correction with incorporation into the ATHENA data analysis software. Journal of Synchrotron Radiation, 2010, 17, 409-413.	2.4	36
30	In/Si(111)-3 Å—3 interface: An unrelaxed T4 geometry. Physical Review Letters, 1993, 71, 1204-1207.	7.8	34
31	Unit cell of strained GeSi. Physical Review B, 1997, 55, 15386-15389.	3.2	32
32	Random-cluster calculation of bond lengths in strained-semiconductor alloys. Physical Review B, 1998, 57, 6266-6269.	3.2	32
33	X-ray standing-wave study of monolayers of Sb on GaAs(110). Physical Review B, 1992, 46, 7276-7279.	3.2	31
34	Determination of the Sb/Si(111) interfacial structure by back-reflection x-ray standing waves and surface extended x-ray-absorption fine structure. Physical Review B, 1991, 44, 3475-3478.	3.2	30
35	Effects of annealing on the local structure of Fe and Co in CoFeB/MgO/CoFeB tunnel junctions: An extended x-ray-absorption fine structure study. Applied Physics Letters, 2010, 96, .	3.3	30
36	Silicide formation and structural evolution in Fe-, Co-, and Ni-implanted silicon. Physical Review B, 1992, 46, 4077-4085.	3.2	29

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37	Separation of the strain and finite size effect on the ferromagnetic properties of La _{0.5} Sr _{0.5} CoO ₃ thin films. <i>Applied Physics Letters</i> , 2007, 91, 172509.	3.3	28
38	Local bonding structure of Sb on Si(111) by surface extended x-ray-absorption fine structure and photoemission. <i>Physical Review B</i> , 1991, 43, 4331-4339.	3.2	27
39	High-resolution structural study of Bi on Si(001). <i>Physical Review B</i> , 1995, 52, R5515-R5518.	3.2	27
40	Layer perfection in ultrathin MOVPE-grown InAs layers buried in GaAs(001) studied by X-ray standing waves and photoluminescence spectroscopy. <i>Journal of Synchrotron Radiation</i> , 1999, 6, 500-502.	2.4	27
41	Diffraction anomalous fine-structure study of strained Ga _{1-x} In _x As on GaAs(001). <i>Physical Review B</i> , 1998, 58, R4215-R4218.	3.2	26
42	Phase-correct bond lengths in crystalline Ge _x Si _{1-x} alloys. <i>Physical Review B</i> , 1998, 57, 14592-14595.	3.2	26
43	Ferromagnetism and Charge Order from a Frozen Electron Configuration in Strained Epitaxial <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"> display="inline"> <mml:mrow> <mml:msub> <mml:mrow> <mml:mi>LaCoO</mml:mi> </mml:mrow> <mml:mrow> <mml:mi>3</mml:mi> </mml:mrow> <mml:mrow> <mml:mi>7.8</mml:mi> </mml:mrow> <mml:mrow> <mml:mi>3</mml:mi> </mml:mrow> </mml:math>. Physical Review Letters, 2018, 120, 197201.	7.8	26
44	Silicon (111) 2 Å–1 surface states: K-edge transitions and surface-selective L _{2,3} VV Auger line shape. <i>Physical Review B</i> , 1989, 39, 8593-8604.	3.2	24
45	Polarization x-ray-absorption near-edge structure study of Pr _{2-x} Ce _x CuO ₄ single crystals: The nature of Ce doping. <i>Physical Review B</i> , 1990, 42, 1037-1040.	3.2	24
46	Structure of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"> display="inline"> <mml:msub> <mml:mi>SrTiO</mml:mi> </mml:msub> </mml:math>. Films on Si. <i>Physical Review Letters</i> , 2012, 108, 166101.	7.8	24
47	Strain and relaxation in InAs and InGaAs films grown on GaAs(001). <i>Applied Physics Letters</i> , 1996, 68, 3010-3012.	3.3	23
48	Evolution of the crystallographic position of As impurities in heavily doped Si crystals as their electrical activity changes. <i>Applied Physics Letters</i> , 1996, 68, 3090-3092.	3.3	23
49	Direct Measurement of Valence-Charge Asymmetry by X-Ray Standing Waves. <i>Physical Review Letters</i> , 2000, 84, 773-776.	7.8	23
50	X-Ray Spectroscopy of Ultra-Thin Oxide/Oxide Heteroepitaxial Films: A Case Study of Single-Nanometer VO ₂ /TiO ₂ . <i>Materials</i> , 2015, 8, 5452-5466.	2.9	23
51	Bond-length strain in buried Ga _{1-x} In _x As thin-alloy films grown coherently on InP(001). <i>Applied Physics Letters</i> , 1998, 73, 1269-1271.	3.3	22
52	Composition dependent bilayer atomic ordering in Al _x Ga _{1-x} N films examined by polarization-dependent extended x-ray absorption fine structure. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	22
53	Annealing dependence of diamond-metal Schottky barrier heights probed by hard x-ray photoelectron spectroscopy. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	22
54	Cr K edge x-ray absorption study of Cr dopants in Mg ₂ SiO ₄ and Ca ₂ GeO ₄ . <i>Applied Physics Letters</i> , 1997, 71, 1168-1170.	3.3	20

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55	Loss for photoemission versus gain for Auger: Direct experimental evidence of crystal-field splitting and charge transfer in photoelectron spectroscopy. <i>Physical Review B</i> , 2015, 91, .	3.2	20
56	Order-to-disorder phase-transition study of Pb on Ge(111). <i>Physical Review B</i> , 1995, 51, 2440-2445.	3.2	19
57	Structural characterization of the (1 monolayer Sb)/GaP(110) interface using x-ray standing waves. <i>Physical Review B</i> , 1992, 46, 6869-6874.	3.2	18
58	Structural determination of the Si(111) $\sqrt{3}\times\sqrt{3}$ -Bi surface by x-ray standing waves and scanning tunneling microscopy. <i>Physical Review B</i> , 1994, 50, 12246-12249.	3.2	18
59	Boron migration due to annealing in CoFeB/MgO/CoFeB interfaces: A combined hard x-ray photoelectron spectroscopy and x-ray absorption studies. <i>Applied Physics Letters</i> , 2011, 99, 222502.	3.3	18
60	Local structure underlying anomalous tetragonal distortions in BiFeO ₃ -PbTiO ₃ ferroelectrics. <i>Applied Physics Letters</i> , 2014, 104, 242913.	3.3	17
61	Si(111) 2Å-1 surface core-level shifts investigated by use of Ge overlayer. <i>Physical Review B</i> , 1989, 40, 12463-12467.	3.2	16
62	Layer perfection in ultrathin InAs quantum wells in GaAs(001). <i>Physical Review B</i> , 2000, 61, 2073-2084.	3.2	16
63	Band alignment of atomic layer deposited HfO ₂ on clean and N passivated germanium surfaces. <i>Applied Physics Letters</i> , 2010, 97, .	3.3	16
64	Design and performance of the Advanced Light Source double-crystal monochromator. <i>Review of Scientific Instruments</i> , 1995, 66, 1748-1750.	1.3	15
65	Lattice compression of Si crystals and crystallographic position of As impurities measured with x-ray standing wave spectroscopy. <i>Journal of Applied Physics</i> , 1999, 85, 1429-1437.	2.5	15
66	Electron lone pair distortion facilitated metal-insulator transition in $\tilde{\chi}^2$ -Pb0.33V2O ₅ nanowires. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	15
67	Morphology and barrier-height development of Bi/InP(110) interfaces. <i>Physical Review B</i> , 1990, 42, 3017-3023.	3.2	13
68	Large-angle bond-rotation relaxation for CdTe(110). <i>Physical Review B</i> , 1995, 51, 10774-10778.	3.2	13
69	Effects of rapid thermal annealing on the structural and local atomic properties of ZnO: Ge nanocomposite thin films. <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	13
70	Analysing trimethylaluminum infiltration into polymer brushes using a scalable area selective vapor phase process. <i>Materials Advances</i> , 2021, 2, 769-781.	5.4	13
71	Atomic-resolution study of lattice distortions of buried In _x Ga _{1-x} As monolayers in GaAs(001). <i>Physical Review B</i> , 1999, 60, 13612-13618.	3.2	12
72	Temperature-dependent local structure of LaFeAsO _{1-x} F _x : Probing the atomic correlations. <i>Journal of Applied Physics</i> , 2010, 108, 123715.	2.5	12

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73	Extended x-ray-absorption fine-structure determination of bond-length conservation at the clean InP(110) surface. Physical Review B, 1992, 46, 9869-9872.	3.2	11
74	Surface extended x-ray-absorption fine-structure study of the (1 monolayer Sb)/GaP(110) interface. Physical Review B, 1993, 47, 6444-6449.	3.2	11
75	Extended x-ray absorption fine-structure measurement of bond-length strain in epitaxial Cd ₂ O ₃ on GaAs(001). Applied Physics Letters, 2000, 76, 2526-2528.	3.3	11
76	Electronic structure of C and N co-doped TiO ₂ : A combined hard x-ray photoemission spectroscopy and density functional theory study. Applied Physics Letters, 2014, 105, .	3.3	11
77	Enhanced electron correlations at the $\text{Sr}_{\text{2-x}}\text{Cd}_{\text{x}}$ Physical Review B, 2015, 91, .		
78	Revealing excitonic processes and chemical bonding in $\text{Mo}_{\text{2-x}}\text{S}_{\text{x}}$ by x-ray spectroscopy. Physical Review B, 2018, 98, .	3.2	11
79	Attenuation of photons at 3–14-keV energies in helium. Physical Review A, 1995, 51, 447-453.	2.5	10
80	Band alignment in Ge/GeO _x /HfO ₂ /TiO ₂ heterojunctions as measured by hard x-ray photoelectron spectroscopy. Applied Physics Letters, 2012, 101, .	3.3	10
81	Nondestructive compositional depth profiling using variable- X_ray photoelectron spectroscopy and maximum entropy regularization. Surface and Interface Analysis, 2014, 46, 407-417.	1.8	10
82	Surface-sensitive x-ray standing-wave study of Si(111)3–3-Ag. Physical Review B, 1996, 53, 15425-15428.	3.2	9
83	Reliability of structural parameters determined from DAFS data using the iterative dispersion integral algorithm. Journal of Synchrotron Radiation, 1999, 6, 335-337.	2.4	9
84	Synchrotron X-ray Based Characterization of CdZnTe Crystals. Journal of Electronic Materials, 2007, 36, 1092-1097.	2.2	9
85	Photon-energy-sensitive SiL _{2,3} VV Auger satellite. Physical Review B, 1989, 39, 6048-6051.	3.2	8
86	X-ray, soft x-ray, and VUV beam position monitor. Review of Scientific Instruments, 1992, 63, 526-529.	1.3	8
87	The role of Ta and Pt in segregation within Co-Cr-Ta and Co-Cr-Pt thin film magnetic recording media. Journal of Applied Physics, 1996, 79, 5345.	2.5	8
88	Evidence of extreme type-III band offset at buried CdO/SnTe interfaces. Physical Review B, 2015, 91, .	3.2	7
89	Surface Segregation in Lanthanum Strontium Manganite Thin Films and Its Potential Effect on the Oxygen Reduction Reaction. Journal of the Electrochemical Society, 2017, 164, F3091-F3096.	2.9	7
90	Preferential site distribution of dilute Pt and Ta in CoCr-based films: An extended x-ray absorption fine structure study. Journal of Applied Physics, 1997, 82, 2912-2917.	2.5	6

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91	Imaging defects in strained-silicon thin films by glancing-incidence x-ray topography. <i>Applied Physics Letters</i> , 2006, 88, 224102.		3.3	5
92	Domain ordering of strained 5 ML SrTiO ₃ films on Si(001). <i>Applied Physics Letters</i> , 2007, 90, 221908.		3.3	5
93	On the scalability of doped hafnia thin films. <i>Applied Physics Letters</i> , 2014, 104, .		3.3	5
94	The impact of porosity on the formation of manganese based copper diffusion barrier layers on low-<i>Îº</i> dielectric materials. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 325102.		2.8	5
95	Semiconductor surface core level shifts by use of selected overlayers. <i>Physica Scripta</i> , 1990, 41, 1034-1036.		2.5	4
96	Atomistic calculation of the local structure in bulk and strained semiconductor alloys. <i>Journal of Applied Physics</i> , 2012, 112, .		2.5	4
97	Zr-induced structural changes in Hf _{1-x} Zr _x O ₂ high-k thin films. <i>Applied Physics A: Materials Science and Processing</i> , 2014, 117, 93-96.		2.3	4
98	Crystal structure and powder diffraction reference pattern of type I clathrate Ba ₈ Ni ₄ Ge ₄₂ . <i>Powder Diffraction</i> , 2012, 27, 25-31.		0.2	2
99	Bond lengths in semiconductor alloys. <i>Journal of Synchrotron Radiation</i> , 1999, 6, 570-572.		2.4	1
100	Evolution of correlated electron behavior from the surface to the bulk in Sr _x Ca _{1-x} VO ₃ . <i>Materials Research Society Symposia Proceedings</i> , 2015, 1730, 1.		0.1	0
101	Noble-metal dark-edge fermiology: Centrifugal barriers, core-hole memory, and the Zeeman Auger effect. <i>Physical Review B</i> , 2021, 104, .		3.2	0